N-Channel Enhancement-Mode Vertical DMOS FET

## Features

- Low threshold ( 2.0 V max.)
- High input impedance and high gain
- Free from secondary breakdown
- Low $\mathrm{C}_{\text {iss }}$ and fast switching speeds


## Applications

- Logic level interfaces - ideal for TTL and CMOS
- Solid state relays
- Battery operated systems
- Photo voltaic drives
- Analog switches
- General purpose line drivers
- Telecom switches


## General Description

This low threshold, enhancement-mode (normally-off) transistor utilizes a vertical DMOS structure and Supertex's well-proven, silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally-induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

## Ordering Information

| Device | Package Options |  |  | $\mathrm{BV}_{\mathrm{DSs}} / \mathrm{BV}_{\mathrm{DGS}}$ <br> (V) | $\mathbf{R}_{\mathrm{DS}(\mathrm{ON})}$ (max) ( $\Omega$ ) | $\begin{aligned} & \mathrm{I}_{\mathrm{DON})} \\ & (\mathrm{min}) \end{aligned}$(A) | $\begin{aligned} & \mathbf{V}_{\mathrm{os}(\mathrm{~h})} \\ & (\max ) \end{aligned}$ |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  | TO-236AB (SOT-23) | TO-92 | TO-243AA (SOT-89) |  |  |  |  |
| TN5325 | TN5325K1-G | TN5325N3-G | TN5325N8-G | 250 | 7.0 | 1.2 | 2.0 |

-G indicates package is RoHS compliant ('Green')


## Absolute Maximum Ratings

| Parameter | Value |
| :--- | ---: |
| Drain-to-source voltage | $\mathrm{BV}_{\mathrm{DSS}}$ |
| Drain-to-gate voltage | $\mathrm{BV}_{\mathrm{DGS}}$ |
| Gate-to-source voltage | $\pm 20 \mathrm{~V}$ |
| Operating and storage temperature | $-55^{\circ} \mathrm{C}$ to $+150^{\circ} \mathrm{C}$ |
| Soldering temperature $^{*}$ | $300^{\circ} \mathrm{C}$ |

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

* Distance of 1.6 mm from case for 10 seconds.


## Pin Configurations



TO-236AB (SOT-23) (K1)
DRAIN


TO-243AA (SOT-89) (N8)

## Product Marking



| SiTN |
| :---: |
| 53 |
| Y 25 |
| YYWW |

YY = Year Sealed

WW = Week Sealed
$\qquad$ = "Green" Packaging


## Thermal Characteristics

| Package | $\underset{(\mathrm{mA})}{\mathrm{I}_{\mathrm{D}}}$ | $I_{D}$ (pulsed) <br> (A) | Power Dissipation <br> $@ T_{A}=25^{\circ} \mathrm{C}$ <br> (W) | $\begin{gathered} \boldsymbol{\theta}_{j c} \\ \left({ }^{\circ} \mathrm{C} / \mathrm{W}\right) \end{gathered}$ | $\begin{gathered} \theta_{j a} \\ \left({ }^{\circ} \mathrm{C} / \mathrm{W}\right) \end{gathered}$ | $\begin{aligned} & \mathrm{I}_{\mathrm{DR}}{ }^{+} \\ & (\mathrm{mA}) \end{aligned}$ | $I_{\text {DRM }}$ <br> (A) |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| TO-236AB (SOT-23) | 150 | 0.4 | 0.36 | 200 | 350 | 150 | 0.4 |
| TO-92 | 215 | 0.8 | 0.74 | 125 | 170 | 215 | 0.8 |
| TO-243AA (SOT-89) | 316 | 1.5 | $1.6{ }^{\ddagger}$ | 15 | $78^{ \pm}$ | 316 | 1.5 |

## Notes:

$\dagger I_{D}$ (continuous) is limited by max rated $T_{j}$
$\ddagger$ Mounted on FR5 Board, $25 \mathrm{~mm} \times 25 \mathrm{~mm} \times 1.57 \mathrm{~mm}$.

Electrical Characteristics ( $T_{A}=25^{\circ} \mathrm{C}$ unless otherwise specified)

| Sym | Parameter | Min | Typ | Max | Units | Conditions |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $B V_{\text {DSs }}$ | Drain-to-source breakdown voltage | 250 | - | - | V | $V_{G S}=0 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=100 \mu \mathrm{~A}$ |
| $V_{\text {GS(th) }}$ | Gate threshold voltage | 0.6 | - | 2.0 | $V$ | $V_{G S}=V_{\text {DS }}, I_{D}=1.0 \mathrm{~mA}$ |
| $\Delta \mathrm{V}_{\text {GS(th) }}$ | Change in $\mathrm{V}_{\text {GS(th) }}$ with temperature | - | - | -4.5 | $\mathrm{mV}^{\circ} \mathrm{C}$ | $V_{G S}=V_{D S}, I_{D}=1.0 \mathrm{~mA}$ |
| $\mathrm{I}_{\text {Gss }}$ | Gate body leakage | - | - | 100 | nA | $V_{G S}= \pm 20 \mathrm{~V}, \mathrm{~V}_{\mathrm{DS}}=0 \mathrm{~V}$ |
| $\mathrm{I}_{\text {Dss }}$ | Zero gate voltage drain current | - | - | 1.0 | $\mu \mathrm{A}$ | $\mathrm{V}_{\text {GS }}=0 \mathrm{~V}, \mathrm{~V}_{\text {DS }}=100 \mathrm{~V}$ |
|  |  | - | - | 10 |  | $\mathrm{V}_{\mathrm{GS}}=0 \mathrm{~V}, \mathrm{~V}_{\mathrm{DS}}=$ Max Rating |
|  |  | - | - | 1.0 | mA | $\begin{aligned} & V_{\text {DS }}=0.8 \text { Max Rating, } \\ & V_{G S}=0 \mathrm{~V}, \mathrm{~T}_{\mathrm{A}}=125^{\circ} \mathrm{C} \end{aligned}$ |
| $I_{\text {DON })}$ | On-state drain current | 0.6 | - | - | A | $\mathrm{V}_{\text {GS }}=4.5 \mathrm{~V}, \mathrm{~V}_{\mathrm{DS}}=25 \mathrm{~V}$ |
|  |  | 1.2 | - | - |  | $V_{G S}=10 \mathrm{~V}, \mathrm{~V}_{\mathrm{DS}}=25 \mathrm{~V}$ |
| $\mathrm{R}_{\text {DS(ON) }}$ | Static drain-to-source on-state resistance | - | - | 8.0 | $\Omega$ | $\mathrm{V}_{\text {GS }}=4.5 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=150 \mathrm{~mA}$ |
|  |  | - | - | 7.0 |  | $\mathrm{V}_{G S}=10 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=1.0 \mathrm{~A}$ |
| $\Delta \mathrm{R}_{\text {DS(ON) }}$ | Change in $\mathrm{R}_{\mathrm{DS}(\mathrm{ON})}$ with temperature | - | - | 1.0 | \%/ ${ }^{\circ} \mathrm{C}$ | $\mathrm{V}_{G S}=4.5 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=150 \mathrm{~mA}$ |
| $\mathrm{G}_{\text {FS }}$ | Forward transductance | 150 | - | - | mmho | $\mathrm{V}_{\mathrm{DS}}=25 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=200 \mathrm{~mA}$ |
| $\mathrm{C}_{\text {ISS }}$ | Input capacitance | - | - | 110 | pF | $\begin{aligned} & V_{\mathrm{GS}}=0 \mathrm{~V}, \\ & \mathrm{~V}_{\mathrm{DS}}=25 \mathrm{~V}, \\ & \mathrm{f}=1.0 \mathrm{MHz} \end{aligned}$ |
| $\mathrm{C}_{\text {oss }}$ | Common source output capacitance | - | - | 60 |  |  |
| $\mathrm{C}_{\text {RSS }}$ | Reverse transfer capacitance | - | - | 23 |  |  |
| $\mathrm{t}_{\mathrm{d}(\mathrm{ON})}$ | Turn-on delay time | - | - | 20 | ns | $\begin{aligned} & \mathrm{V}_{\mathrm{DD}}=25 \mathrm{~V}, \\ & \mathrm{I}_{\mathrm{D}}=150 \mathrm{~mA}, \\ & \mathrm{R}_{\mathrm{GEN}}=25 \Omega \end{aligned}$ |
| $\mathrm{t}_{\mathrm{r}}$ | Rise time | - | - | 15 |  |  |
| $\mathrm{t}_{\text {d(OFF) }}$ | Turn-off delay time | - | - | 25 |  |  |
| $\mathrm{t}_{\mathrm{f}}$ | Fall time | - | - | 25 |  |  |
| $\mathrm{V}_{\text {SD }}$ | Diode forward voltage drop | - | - | 1.8 | V | $V_{G S}=0 \mathrm{~V}, \mathrm{I}_{\text {SD }}=200 \mathrm{~mA}$ |
| $\mathrm{t}_{\text {tr }}$ | Reverse recovery time | - | 300 | - | ns | $V_{G S}=0 \mathrm{~V}, \mathrm{I}_{\text {SD }}=200 \mathrm{~mA}$ |
| Notes: <br> 1. All | C. parameters $100 \%$ tested at $25^{\circ} \mathrm{C}$ unless oth C. parameters sample tested. | tated. | Ise test | 300 s | se, $2 \%$ du | ty cycle.) |

## Switching Waveforms and Test Circuit



## 3-Lead TO-236AB (SOT-23) Package Outline (K1)

## $2.90 \times 1.30 \mathrm{~mm}$ body, 1.12 mm height (max), 1.90mm pitch



| Symbol |  | A | A1 | A2 | b | D | E | E1 | e | e1 | L | L1 | $\boldsymbol{\theta}$ |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Dimension (mm) | MIN | 0.89 | 0.01 | 0.88 | 0.30 | 2.80 | 2.10 | 1.20 | $\begin{aligned} & 0.95 \\ & \text { BSC } \end{aligned}$ | $\begin{aligned} & 1.90 \\ & \text { BSC } \end{aligned}$ | $0.20{ }^{+}$ | $\begin{aligned} & 0.54 \\ & \text { REF } \end{aligned}$ | $0^{\circ}$ |
|  | NOM | - | - | 0.95 | - | 2.90 | - | 1.30 |  |  | 0.50 |  | - |
|  | MAX | 1.12 | 0.10 | 1.02 | 0.50 | 3.04 | 2.64 | 1.40 |  |  | 0.60 |  | $8^{\circ}$ |

[^0]$\dagger$ This dimension differs from the JEDEC drawing.
Drawings not to scale.
Supertex Doc.\#: DSPD-3TO236ABK1, Version C041309.

## 3-Lead TO-92 Package Outline (N3)



Front View


Side View


Bottom View

| Symbol |  | A | b | c | D | E | E1 | e | e1 | L |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Dimensions (inches) | MIN | . 170 | . $014{ }^{+}$ | . $014{ }^{+}$ | . 175 | . 125 | . 080 | . 095 | . 045 | . 500 |
|  | NOM | - | - | - | - | - | - | - | - | - |
|  | MAX | . 210 | . $022^{\dagger}$ | . $022^{\dagger}$ | . 205 | . 165 | . 105 | . 105 | . 055 | .610* |

JEDEC Registration TO-92.

* This dimension is not specified in the JEDEC drawing
$\dagger$ This dimension differs from the JEDEC drawing.
Drawings not to scale.
Supertex Doc.\#: DSPD-3TO92N3, Version E041009.


## 3-Lead TO-243AA (SOT-89) Package Outline (N8)



Top View


Side View

| Symbol |  | A | b | b1 | C | D | D1 | E | E1 | e | e1 | H | L |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Dimensions (mm) | MIN | 1.40 | 0.44 | 0.36 | 0.35 | 4.40 | 1.62 | 2.29 | $2.00^{+}$ | $\begin{aligned} & 1.50 \\ & \text { BSC } \end{aligned}$ | $\begin{aligned} & 3.00 \\ & \text { BSC } \end{aligned}$ | 3.94 | 0.89 |
|  | NOM | - | - | - | - | - | - | - | - |  |  | - | - |
|  | MAX | 1.60 | 0.56 | 0.48 | 0.44 | 4.60 | 1.83 | 2.60 | 2.29 |  |  | 4.25 | 1.20 |

JEDEC Registration TO-243, Variation AA, Issue C, July 1986.
$t$ This dimension differs from the JEDEC drawing
Drawings not to scale.
Supertex Doc. \#: DSPD-3TO243AAN8, Version E051509.
(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to http://www.supertex.com/packaging.html.)

[^1]
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[^0]:    JEDEC Registration TO-236, Variation AB, Issue H, Jan. 1999.

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